



Curriculum Vitae

Franklin L. Duan was born in China, in 1962. He received the B.S. and M.S. in the Department of Electrical Engineering from Tsinghua University, Beijing, China, in 1985 and 1987 respectively. He subsequently joined the Institute of Semiconductors, Chinese Academy of Sciences, in Beijing China, from 1987 to 1991, where he engaged in developing new high speed devices and conducted research on new phenomenon in the combined system of III-V heterostructures (two dimensional system) and superconductors. Then he worked as an engineer in Chartered Semiconductor Manufacturing, Singapore, in 1992, on the 0.8 micron VLSI manufacturing and customer services. He is presently completing his Ph.D. degree in Department of Electrical and Computer Engineering at George Mason University, Fairfax, VA. His current research interests are the device simulations and reliability issues relating hot-carrier degradation and floating body effect in SOI MOSFET.

A black and white image of a handwritten signature in cursive script. The signature reads "Franklin L. Duan". The letters are fluid and connected, with a prominent flourish at the end of the name.